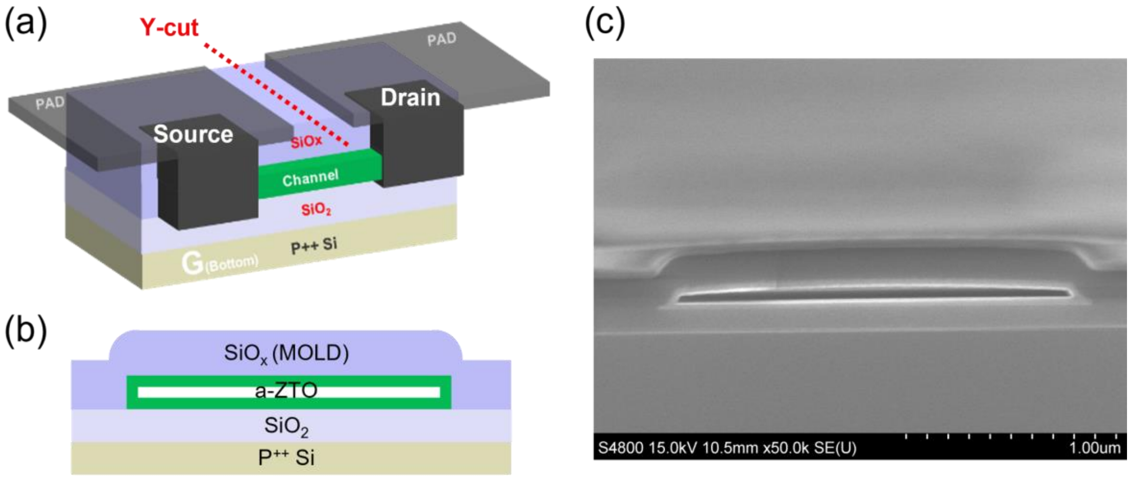

Figure 1. Schematic diagram of (a) mold-structure TFTs, (b) y-cut mold and (c) Scanning Electron Microscope image of (b). This shows that an a-ZTO channel can be deposited within the mold by ALD.

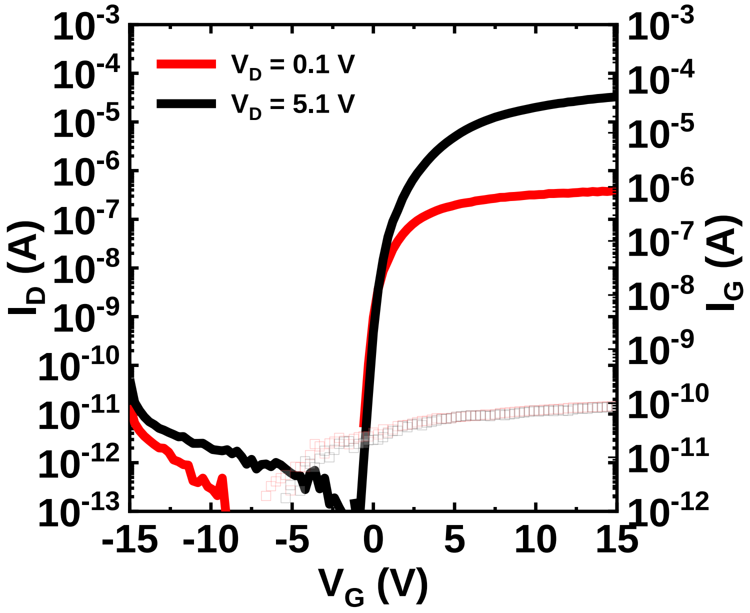

Figure 2. Transfer curves of a-ZTO TFTs with mold structure.
It demonstrates that mold-structure TFTs can achieve stable switching performance and reliable device operation.

Acknowledgments: This work was supported by the Next-generation Intelligence Semiconductor Foundation (2022M3F3A2A01079620).

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